

IN THE SPECIFICATION

Please replace the paragraph [0033] at pages 6-7, with the following rewritten paragraph:

[0033] In another aspect of the present invention (hereinafter referred to as “second invention”), a method for fabricating a semiconductor optical device is provided including the steps of: forming a first stacked structure including either of a DFB laser having a quantum-well-structure active layer made of a GaInAsP-based material ~~and~~ or an EA modulator having a quantum-well-structure active layer made of an AlGaInAs-based material in a DFB laser formation area and in an EA modulator formation area, respectively, on a semiconductor substrate; forming a second stacked structure by etching the area corresponding to the other of the DFB laser ~~and~~ or the EA modulator to expose the substrate ~~in the DFB laser formation area this area or in the EA modulator formation area~~; forming a third stacked structure including the other of the DFB laser ~~and~~ or the EA modulator on the exposed substrate; and forming a mesa stripe by simultaneously etching the second and third stacked structures.